

CMOS Quad Bilateral Switch

For Transmission or Multiplexing of Analog or Digital Signals

The RCA-CD4016A Series types are quad bilateral switches intended for the transmission or multiplexing of analog or digital signals. Each of the four independent bilateral switches has a single control signal input which simultaneously biases both the p and n device in a given switch ON or OFF. These types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), 14-lead ceramic flat packages (K suffix), and in chip form (H suffix).

Features:

- 15-V digital or ± 7.5 -V peak-to-peak switching
- 280- Ω typical ON resistance for 15-V operation
- Switch ON resistance matched to within 10 Ω typ. over 15-V signal-input range
- High ON/OFF output-voltage ratio: 65 dB typ. @ $f_{is} = 10$ kHz, $R_L = 10$ k Ω

- High degree of linearity: $<0.5\%$ distortion typ. @ $f_{is} = 1$ kHz, $V_{is} = 5$ V_{p-p}, $V_{DD} - V_{SS} \geq 10$ V, $R_L = 10$ k Ω
- Extremely low OFF switch leakage resulting in very low offset current and high effective OFF resistance: 100 pA typ. @ $V_{DD} - V_{SS} = 10$ V, $T_A = 25^\circ\text{C}$
- Extremely high control input impedance (control circuit isolated from signal circuit: 1012 Ω typ.)
- Low crosstalk between switches: -50 dB typ. @ $f_{is} = 0.9$ MHz, $R_L = 1$ k Ω
- Matched control-input to signal-output capacitance: Reduces output signal transients
- Frequency response, switch ON = 40 MHz (typ.)
- Quiescent current specified to 15 V
- Maximum input leakage current of 1 μA at 15 V (full package-temperature range)

Applications:

- Analog signal switching/multiplexing
- Signal gating
- Squelch control
- Chopper
- Modulator
- Demodulator
- Commutating switch

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following range:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
Supply Voltage Range (For $T_A = \text{Full Package Temperature Range}$)	3	12	V

TYPICAL "ON" RESISTANCE CHARACTERISTICS

CHARACTERISTIC*	SUPPLY CONDITIONS		LOAD CONDITIONS					
	V_{DD} (V)	V_{SS} (V)	$R_L = 1\text{k}\Omega$		$R_L = 10\text{k}\Omega$		$R_L = 100\text{k}\Omega$	
			VALUE (1)	V_{is} (V)	VALUE (1)	V_{is} (V)	VALUE (1)	V_{is} (V)
R_{ON}	+15	0	200	+15	200	+15	180	+15
			200	0	200	0	200	0
$R_{ON(max)}$	+15	0	300	+11	300	+9.3	320	+9.2
			290	+10	250	+10	240	+10
R_{ON}	+10	0	290	0	250	0	300	0
$R_{ON(max)}$	+10	0	500	+7.4	560	+5.6	610	+5.5
			860	+5	470	+5	450	+5
R_{ON}	+5	0	600	0	580	0	800	0
$R_{ON(max)}$	+5	0	1.7k	+4.2	7k	+2.9	33k	+2.7
R_{ON}	+7.5	-7.5	200	+7.5	200	+7.5	180	+7.5
			200	-7.5	200	-7.5	180	-7.5
$R_{ON(max)}$	+7.5	-7.5	290	+0.25	280	+0.25	400	+0.25
			260	+5	250	+5	240	+5
R_{ON}	+5	-5	310	-5	250	-5	240	-5
$R_{ON(max)}$	+5	-5	600	+0.25	580	+0.25	760	+0.25
			590	+2.5	450	+2.5	490	+2.5
R_{ON}	+2.5	-2.5	720	-2.5	520	-2.5	520	-2.5
$R_{ON(max)}$	+2.5	-2.5	232k	+0.25	300k	+0.25	870k	+0.25

* Variation from a perfect switch, $R_{ON} = 0\Omega$.

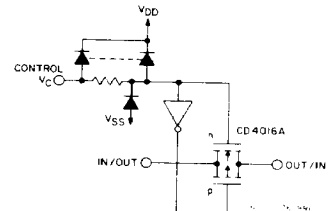
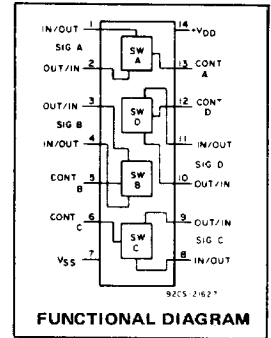


Fig. 1—Schematic diagram — 1 of 4 identical sections.

- Digital signal switching/multiplexing
- CMOS logic implementation
- Analog-to-digital & digital-to-analog conversion
- Digital control of frequency, impedance, phase, and analog-signal gain

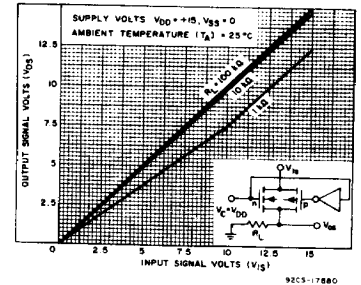


Fig. 2—Typ. "ON" characteristics for 1 of 4 switches with $V_{DD} = +15$ V, $V_{SS} = 0$ V.

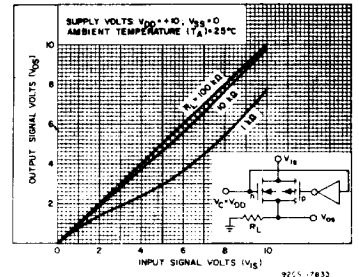


Fig. 3—Typ. "ON" characteristics for 1 of 4 switches with $V_{DD} = +10$ V, $V_{SS} = 0$ V.

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ELECTRICAL CHARACTERISTICS (All inputs. $V_{SS} \leq V_I \leq V_{DD}$) Recommended DC Supply Voltage ($V_{DD}-V_{SS}$), 3 to 15 V)

Characteristic	Test Conditions <i>All Voltage Values are in Volts</i>	Limits <i>Values at -55°C, +25°C, +125°C Apply to D, F, K, H Packages Values at -40°C, +25°C, +85°C Apply to E Package</i>						Unit		
		V _{DD} (V)	-55°	-40°	+85°	+125°	+25°C			
							Typ.		Max.	
Quiescent Device Current, I _L max (All switches ON or all Switches OFF) D, F, H Pkgs.		5	0.25	—	—	10	0.01	0.25	μA	
		10	0.5	—	—	20	0.01	0.5		
		15	2	—	—	40	0.01	2		
		5	—	0.25	5	—	—	0.25		
E, V Pkgs.		10	—	0.5	10	—	—	0.5	μA	
		15	—	2	20	—	—	2		
		Signal Inputs (V _{IS}) and Outputs (V _{OS})								
ON Resistance, R _{ON}	V _C = V _{DD} R _L = 10 kΩ	V _{SS}	V _{IS}	Typ/Max	Typ/Max	Typ/Max	Typ/Max			Ω
	+7.5	-7.5	+7.5	120/360	130/370	260/520	300/600	200	400	
			-7.5	120/360	130/370	260/520	300/600	200	400	
			±0.25	130/775	160/790	400/1080	470/1230	280	850	
	+5	-5	+5	130/600	150/610	340/840	400/960	250	660	
			-5	130/600	150/610	340/840	400/960	250	660	
			±0.25	325/1870	370/1900	770/2380	900/2600	580	2000	
	+15	0	+15	120/360	130/370	260/520	300/600	200	400	
			±0.25	120/360	130/370	260/520	300/600	200	400	
			+9.3	150/775	180/790	400/1080	490/1230	300	850	
	+10	0	+10	130/600	150/610	340/840	400/960	250	660	
			±0.25	130/600	150/610	340/840	400/960	250	660	
			+5.6	300/1870	350/1900	750/2380	880/2600	560	2000	
ΔRON Resistance Between Any 2 of 4 Switches ΔRON	R _L = 10 kΩ								Ω	
	+7.5	-7.5	±7.5	—	—	—	10	—		
	+5	-5	±5	—	—	—	15	—		
Sine Wave Response (Distortion)	+5	-5	5 p-p	—	—	—	—	—	%	
	R _L = 10 kΩ f _{IS} = 1 kHz			—	—	—	—	0.4		
Frequency Response Switch ON (Sine-Wave Input)	V _{DD} = +5 V _C = V _{SS} = -5		-5 p-p	—	—	—	—	—	MHz	
	R _L = 1 kΩ			—	—	—	—	—		
	20 log ₁₀ $\frac{V_{OS}}{V_{IS}}$ = -3 dB			—	—	—	—	40		
Feedthrough Switch OFF	+5	-5	-5 p-p	—	—	—	—	—	MHz	
	R _L = 1 kΩ 20 log ₁₀ $\frac{V_{OS}}{V_{IS}}$ = -50 dB			—	—	—	—	1.25		
Input or Output Leakage Current Switch OFF (Effective OFF Resistance)	V _{DD}	V _C = V _{SS}							μA	
	+7.5	-7.5	±7.5	—	—	—	—	±100		
	+5	-5	±5	—	—	—	—	±10x10 ⁻³		
								±125*	nA	

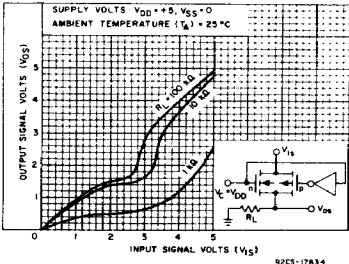


Fig. 4 — Typ. "ON" characteristics for 1 of 4 switches with $V_{DD} = +5\text{ V}$, $V_{SS} = 0\text{ V}$.

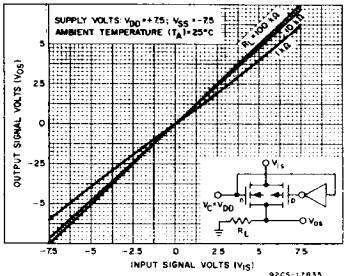


Fig. 5 — Typ. "ON" characteristics for 1 of 4 switches with $V_{DD} = +7.5\text{ V}$, $V_{SS} = -7.5\text{ V}$.

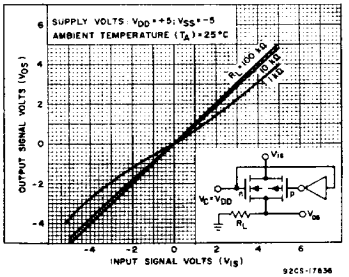


Fig. 6 — Typ. "ON" characteristics for 1 of 4 switches with $V_{DD} = +5\text{ V}$, $V_{SS} = -5\text{ V}$.

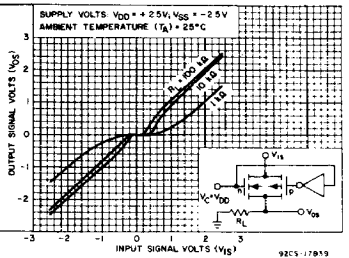


Fig. 7 — Typ. "ON" characteristics for 1 of 4 switches with $V_{DD} = +2.5\text{ V}$, $V_{SS} = -2.5\text{ V}$.

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ELECTRICAL CHARACTERISTICS (Cont'd) $V_{SS} \leq V_I \leq V_{DD}$ Recommended DC Supply Voltage ($V_{DD}-V_{SS}$) . . 3 to 15 V

Characteristic	Test Conditions All Voltage Values are in Volts	Limits Values at -55°C, +25°C, +125°C Apply to D, F, K, H Packages Values at -40°C, +25°C, +85°C Apply to E Package						Unit	
		VDD (V)	-55°	-40°	+85°	+125°	+25°C		
							Typ.		Max.
Crosstalk Between Any 2 of 4 Switches (f = -50 dB)	VC(A) = VDD + 5 VC(B) = VSS - 5 VIS(A) = 5 p-p RL = 1 kΩ $20 \log_{10} \frac{V_{OS}(B)}{V_{IS}(A)}$ -50 dB		-	-	-	-	0.9	-	MHz
Propagation Delay (Signal Input to Signal Output) tpd	VC = VDD VSS = GND CL = 50 pF VIS = 10 Sq. Wave tr, tf = 20 ns	VDD 5 10					20 10	50 25	ns
Capacitance: Input, CIs	VDD = +5		-	-	-	-	4	-	pF
Output, Cos	VCC = VSS = -5		-	-	-	-	4	-	
Feedthrough, Cigs			-	-	-	-	0.2	-	
Control (VC)†									
Switch Threshold Voltage, VTH	VIS ≤ VDD, IIS = 10 μA VDD = VSS = 15, 10, 5		0.7 min 2.9 max	-	-	0.2 min 2.4 max	0.5 min 1.5	2.7	V
Input Leakage Current, IIL max	VIS ≤ VDD VDD = 15		±10 ⁻⁵ typ; ±1 max.						μA
Crosstalk (Control Input to Signal Output)	VC = 10 (Sq. Wave) tr, tf = 20 ns RL = 10 kΩ VDD = 10		-	-	-	-	50	-	mV
Turn-On Propagation Delay, tp dc	VDD = VSS = 10 VC = 10 (See Fig. 25) tr, tf = 20 ns CL = 15 pF RL = 1 kΩ	VDD 5 10	-	-	-	-	20 10	40 20	ns
Maximum Allowable Control Input Repetition Rate	VDD = 10, VSS = GND RL = 1 kΩ, CL = 15 pF VCC = 10 (Sq. Wave) tr, tf = 20 ns		-	-	-	-	10	-	MHz
Av. Input Capacitance, CI			-	-	-	-	5	-	pF

* Limit determined by minimum feasible leakage current measurement for automatic testing.

▲ Symmetrical about 0 volts.

● For all test conditions.

† All control inputs protected by COS/MOS protection network.

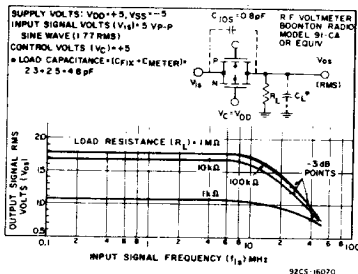


Fig. 11 — Typical switch frequency response — switch "ON".

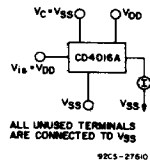


Fig. 12 — "OFF" switch input or output leakage current test circuit.

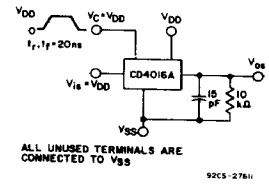


Fig. 13 — Test circuit for square-wave response.

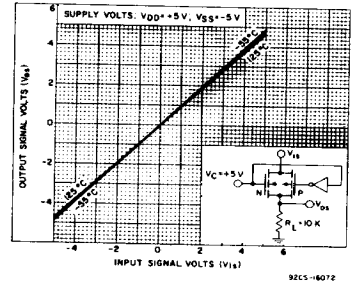


Fig. 8 — Typ. "ON" characteristics as a function of temp. for 1 of 4 switches with $V_{DD} = +5\text{ V}$, $V_{SS} = -5\text{ V}$.

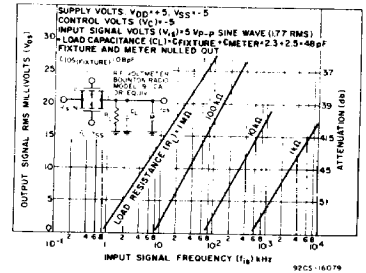


Fig. 9 — Typ. feedthru vs. frequency — switch "OFF".

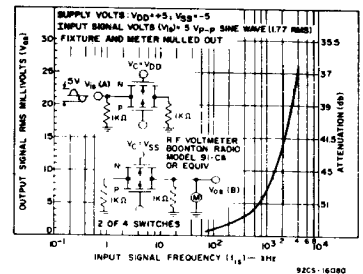


Fig. 10 — Typical crosstalk between switch circuits in the same package.

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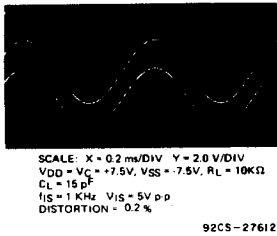


Fig. 14 – Typical sine wave response of $V_{DD} = +7.5\text{ V}$, $V_{SS} = -7.5\text{ V}$.

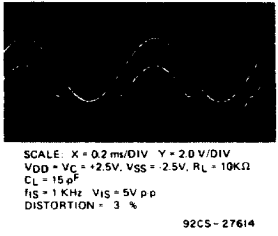


Fig. 15 – Typical sine wave response of $V_{DD} = +2.5\text{ V}$, $V_{SS} = -2.5\text{ V}$.

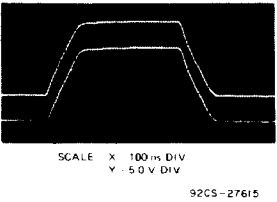


Fig. 16 – Typical square wave response at $V_{DD} = V_C = +15\text{ V}$, $V_{SS} = \text{Gnd}$.

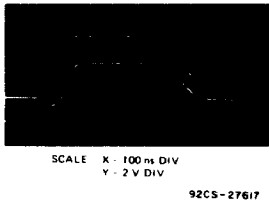
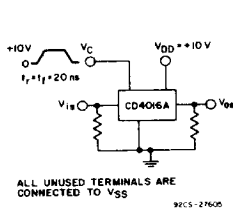
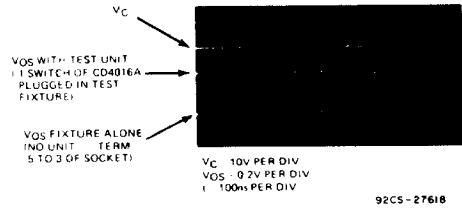


Fig. 17 – Typical square wave response at $V_{DD} = V_C = +5\text{ V}$, $V_{SS} = \text{Gnd}$.



(a)

Fig. 18 – Crosstalk-control input to signal output.



(b)

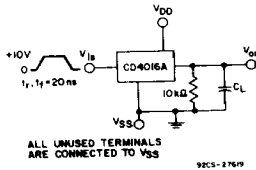


Fig. 19 – Propagation delay time signal input (V_{IS}) to signal output (V_{OS}).

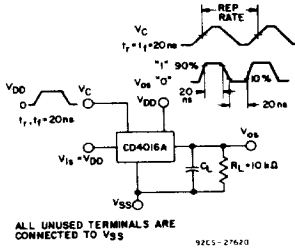


Fig. 20 – Max. allowable control input repetition rate.

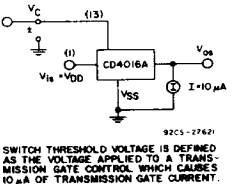


Fig. 21 – Switch threshold voltage.

MAXIMUM RATINGS, Absolute-Maximum Values:

STORAGE-TEMPERATURE RANGE (T_{stg})	-65 to +150°C
OPERATING-TEMPERATURE RANGE (T_A)	
PACKAGE TYPES D, F, K, H	-55 to +125°C
PACKAGE TYPE E	-40 to +85°C
DC SUPPLY-VOLTAGE RANGE, (V_{DD})	
(Voltages referenced to V_{SS} Terminal)	-0.5 to +15 V
POWER DISSIPATION PER PACKAGE (P_D)	
FOR $T_A = -40$ to +60°C (PACKAGE TYPE E)	500 mW
FOR $T_A = +60$ to +85°C (PACKAGE TYPE E)	Derate Linearly at 12 mW/°C to 200 mW
FOR $T_A = -55$ to +100°C (PACKAGE TYPES D, F, K)	500 mW
FOR $T_A = +100$ to +125°C (PACKAGE TYPES D, F, K)	Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (ALL PACKAGE TYPES)}$	100 mW
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5 to $V_{DD} + 0.5\text{ V}$
LEAD TEMPERATURE (DURING SOLDERING)	+265°C
At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10 s max.	

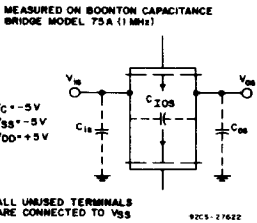


Fig. 22 – Capacitance C_{IOs} and C_{OS} .